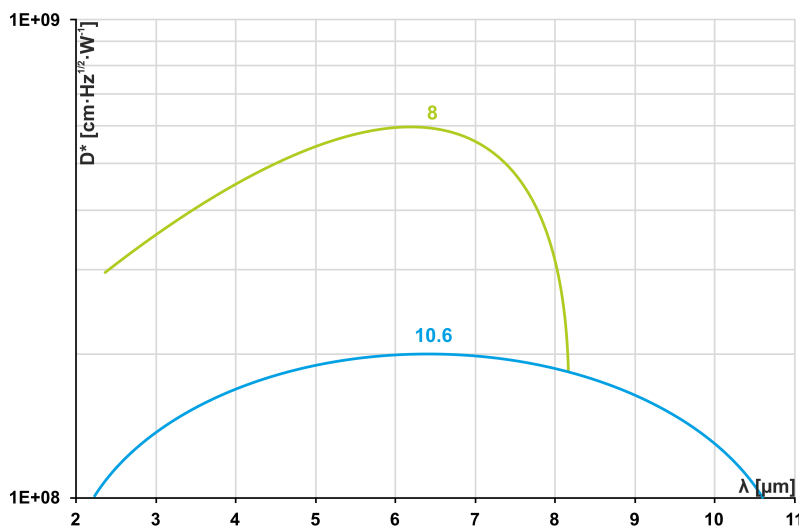


PVMI Series

8 – 11 μm IR PHOTOVOLTAIC MULTIPLE JUNCTION DETECTORS OPTICALLY IMMERSED



Example of D^* vs Wavelength λ for PVMI Series HgCdTe Detectors. Spectral Characteristics of individual detectors may vary from those shown on the chart.

Features

- Ambient temperature operation
- No bias required
- Short time constant
- No flicker noise
- Operation from DC to VHF
- Perfect match to fast electronics
- Wide dynamic range
- Low cost
- Custom design upon request

Description

The PVMI- λ_{opt} photodetectors series (λ_{opt} - optimal wavelength in micrometers) feature IR multiple junction optically immersed photovoltaic detector. The devices are optimized for the maximum performance at λ_{opt} . Highest performance and stability are achieved by application of variable gap HgCdTe semiconductor, optimized doping and sophisticated surface processing. Standard detectors are available in TO39 or BNC packages without windows. Various windows, other packages and connectors are available upon request.

IR Detector Specification @20°C

Parameter	Symbol	Unit	PVMI-8	PVMI-10.6
Optimal Wavelength	λ_{opt}	μm	8	10.6
Detectivity ¹⁾ : @ λ_{peak} @ λ_{opt}	D^*	$\frac{\text{cm} \cdot \sqrt{\text{Hz}}}{\text{W}}$	$\geq 6.0 \times 10^8$ $\geq 3.0 \times 10^8$	$\geq 2.0 \times 10^8$ $\geq 1.0 \times 10^8$
Current Responsivity - Width Product @ λ_{opt} 1x1mm	$R_i \cdot w$	$\frac{\text{A} \cdot \text{mm}}{\text{W}}$	≥ 0.04	≥ 0.01
Time Constant	τ	ns	≤ 4	≤ 1.5
Resistance	R	Ω	50 to 300	20 to 150
Operating Temperature	T	K		~300
Acceptance Angle, F/#	$\Phi, -$	deg, -		36, 1.62

¹⁾ Data Sheet states minimum guaranteed D^* values for each detector model. Higher performance detectors can be provided upon request.

Type	Optical Area [mmxmm]									
	0.025x0.025	0.05x0.05	0.1x0.1	0.2x0.2	0.25x0.25	0.5x0.5	1x1	2x2	3x3	4x4
PVMI-8					O	O	X	X		
PVMI-10.6					O	O	X	X		

X – standard detectors

O – detectors available upon request, parameters may vary from these in Data Sheet